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PATENT
0941-0924P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: LEE, Min-Hung et al. Conf.: 3667
Appl. No.: 10/791,816 Group: 2811
Filed: March 4, 2004 Examiner: Shouxian Hu
For: STRAINED SILICON CARBON ALLOY MOSFET
STRUCTURE AND FABRICATION METHOD THEREOF

LARGE ENTITY TRANSMITTAL FORM

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

February 11, 2005

Sir:

Transmitted herewith is a Reply to Restriction/Election Requirement in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ Petition for _____ () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ A check in the amount of \$0.00 is enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. A triplicate copy of this sheet is attached.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By 
Joe McKinney Muncy #32,334

KM/asc
0941-0924P

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Attachment(s)



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THEREOF

REPLY TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

February 11, 2005

Sir:

Responsive to the Office Action dated January 11, 2005, the following election and remarks are respectfully submitted in connection with the above-identified application.

REMARKS

Claims 1-16 are now pending in the present application.

The Examiner has given the following Restriction Requirement:

Group I, claims 1-8, drawn to a semiconductor device; and

Group II, claims 9-16, drawn to a method of making a semiconductor device.

In response to this requirement, Applicants hereby elect Group I, claims 1-8 drawn to a semiconductor device. This election is with traverse.